

FDS7766

30V N-Channel PowerTrench[®] MOSFET

General Description

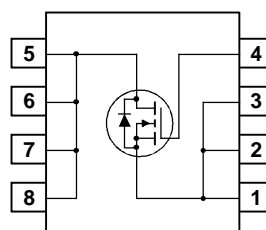
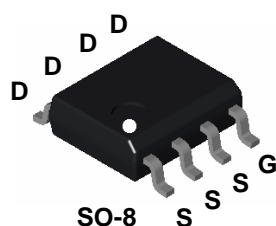
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for "low side" synchronous rectifier operation, providing an extremely low $R_{DS(ON)}$ in a small package.

Applications

- Synchronous rectifier
- DC/DC converter

Features

- 17 A, 30 V $R_{DS(ON)} = 5.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 6.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability
- Fast switching



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 16	V
I_D	Drain Current – Continuous (Note 1a)	17	A
	– Pulsed	60	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.2	
		1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to $+175$	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1c)	125	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS7766	FDS7766	13"	12mm	2500 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		24		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 16\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -16\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.5	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-4.3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 17\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 15.5\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 17\text{ A}, T_J = 125^\circ\text{C}$		4.2 4.7 5.7	5.5 6.5 7.2	m Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	30			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 17\text{ A}$		116		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		4973		pF
C_{oss}	Output Capacitance			826		pF
C_{rss}	Reverse Transfer Capacitance			341		pF

Switching Characteristics (Note 2)

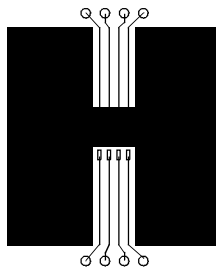
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		12	22	ns
t_r	Turn–On Rise Time			8	16	ns
$t_{d(off)}$	Turn–Off Delay Time			85	136	ns
t_f	Turn–Off Fall Time			25	40	ns
Q_g	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 17\text{ A},$ $V_{GS} = 5.0\text{ V}$		43	69	nC
Q_{gs}	Gate–Source Charge			13		nC
Q_{gd}	Gate–Drain Charge			11		nC

Drain–Source Diode Characteristics and Maximum Ratings

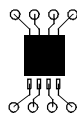
I_S	Maximum Continuous Drain–Source Diode Forward Current			2.5		A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.5\text{ A}$ (Note 2)		0.7	1.2	V

Notes:

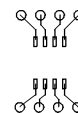
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 105°C/W when mounted on a $.04\text{ in}^2$ pad of 2 oz copper

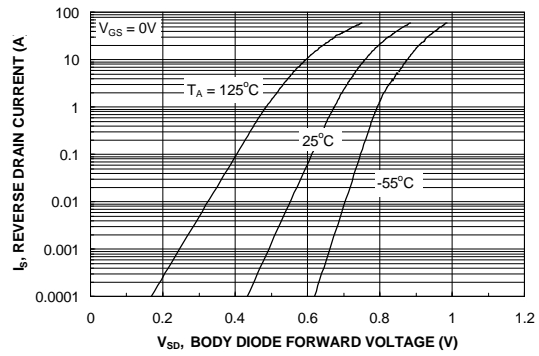
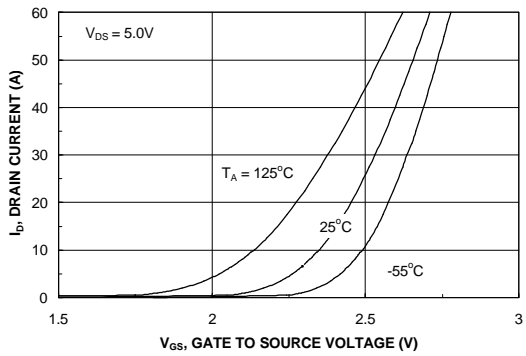
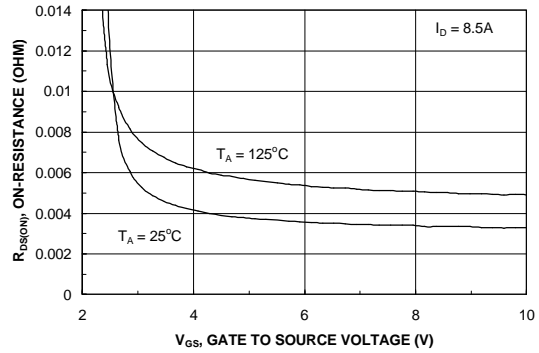
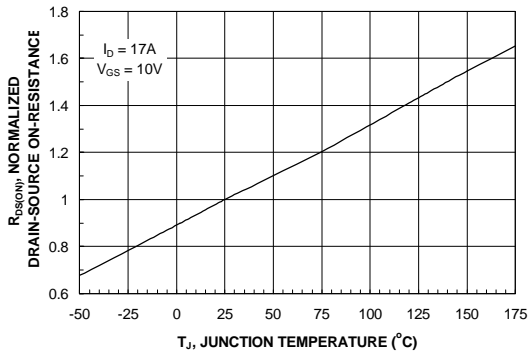
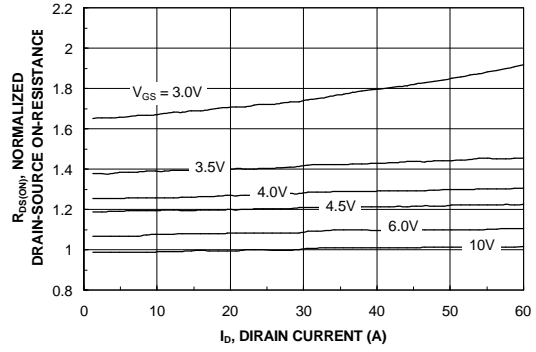
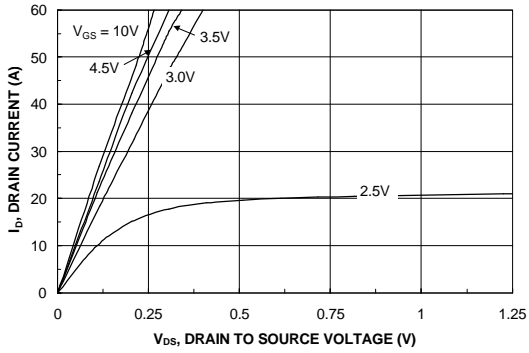


c) 125°C/W when mounted on a minimum pad.

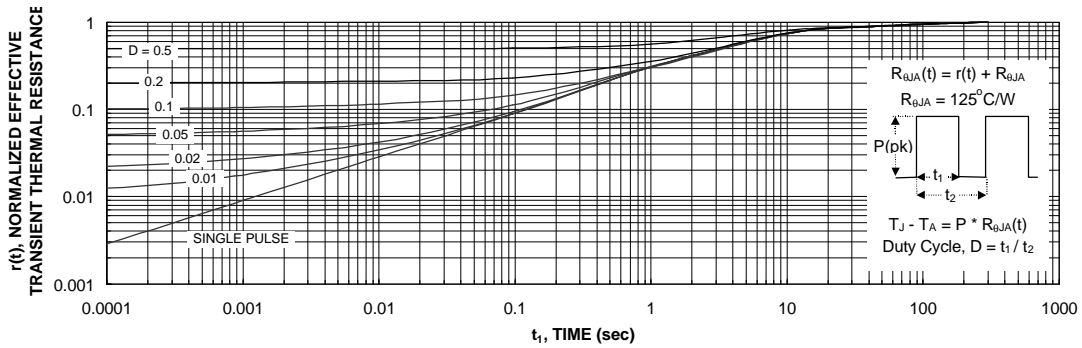
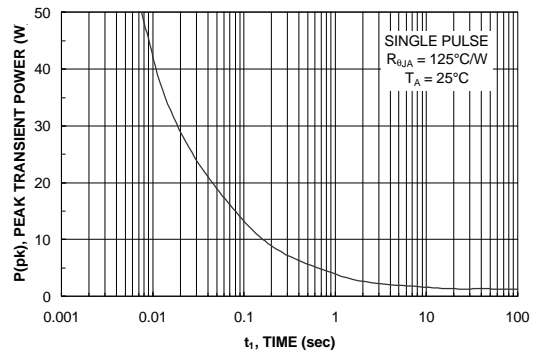
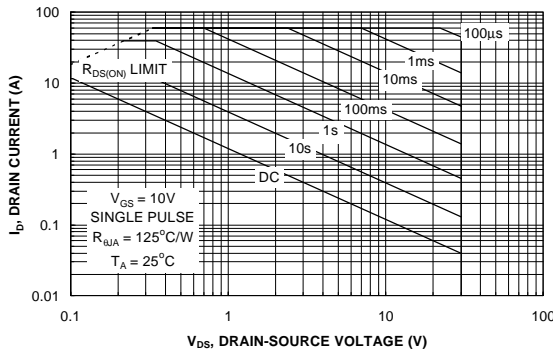
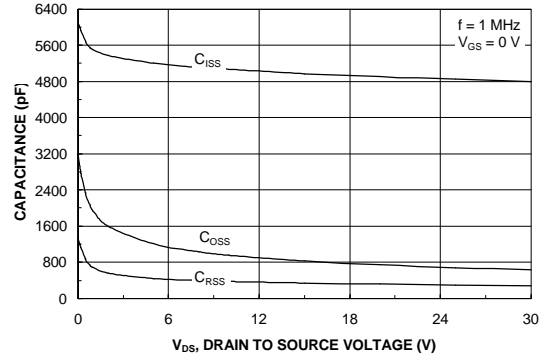
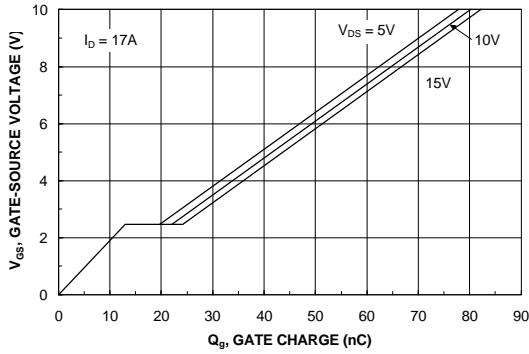
Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < $300\ \mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics



Typical Characteristics



Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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